

ABSTRACT

A method for producing a single crystal in which when the single crystal is grown by Czochralski method, V/G is controlled by controlling a fluctuation of a temperature gradient G of the crystal which is being pulled without lowering a pulling rate V, thereby the single crystal including a desired defect region over a whole plane in a radial direction of the crystal entirely in a direction of the crystal growth axis can be produced effectively for a short time at a high yield.